

Nadim Chowdhury

List of Publications by Year in descending order

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28
papers

1,651
citations

623734

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docs citations

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times ranked

1666
citing authors

#	ARTICLE	IF	CITATIONS
1	Self-Aligned E-Mode GaN p -Channel FinFET With $I_{ON} > 100$ mA/mm and $I_{ON}/I_{OFF} > 10^4$. IEEE Electron Device Letters, 2022, 43, 358-361.	3.9	22
2	Tungsten-Gated GaN/AlGaN p -FET With $I_{max} > 120$ mA/mm on GaN-on-Si. IEEE Electron Device Letters, 2022, 43, 545-548.	3.9	19
3	GaN 2.0: Power FinFETs, Complementary Gate Drivers and Low-Cost Vertical Devices. , 2021, , .		7
4	Performance Estimation of GaN CMOS Technology. , 2021, , .		4
5	Emerging GaN technologies for power, RF, digital, and quantum computing applications: Recent advances and prospects. Journal of Applied Physics, 2021, 130, .	2.5	89
6	Prospects for Wide Bandgap and Ultrawide Bandgap CMOS Devices. IEEE Transactions on Electron Devices, 2020, 67, 4010-4020.	3.0	73
7	Recent Development in 2D and 3D GaN devices for RF and Power Electronics Applications. , 2020, , .		0
8	Barrier heights and Fermi level pinning in metal contacts on p -type GaN. Applied Physics Letters, 2020, 116, .	3.3	15
9	Materials and Technology Issues for the Next Generation of Power Electronic Devices. , 2020, , .		0
10	Regrowth-Free GaN-Based Complementary Logic on a Si Substrate. IEEE Electron Device Letters, 2020, 41, 820-823.	3.9	74
11	Field-induced Acceptor Ionization in Enhancement-mode GaN p -MOSFETs. , 2020, , .		19
12	Nitrogen-Polar Polarization-Doped Field-Effect Transistor Based on $Al_{0.8}Ga_{0.2}N/AlN$ on SiC With Drain Current Over 100 mA/mm. IEEE Electron Device Letters, 2019, 40, 1245-1248.	3.9	32
13	Superior Performance of 5-nm Gate Length GaN Nanowire nFET for Digital Logic Applications. IEEE Electron Device Letters, 2019, 40, 874-877.	3.9	13
14	p -Channel GaN Transistor Based on p -GaN/AlGaN/GaN on Si. IEEE Electron Device Letters, 2019, 40, 1036-1039.	3.9	88
15	First Demonstration of a Self-Aligned GaN p -FET. , 2019, , .		25
16	720-V/0.35-mA/cm ² Fully Vertical GaN-on-Si Power Diodes by Selective Removal of Si Substrates and Buffer Layers. IEEE Electron Device Letters, 2018, 39, 715-718.	3.9	69
17	The 2018 GaN power electronics roadmap. Journal Physics D: Applied Physics, 2018, 51, 163001.	2.8	843
18	Materials and processing issues in vertical GaN power electronics. Materials Science in Semiconductor Processing, 2018, 78, 75-84.	4.0	112

#	ARTICLE	IF	CITATIONS
19	Large Area 1.2 kV GaN Vertical Power FinFETs with a Record Switching Figure-of-Merit. IEEE Electron Device Letters, 2018, , 1-1.	3.9	69
20	GaN Nanowire n-MOSFET With 5 nm Channel Length for Applications in Digital Electronics. IEEE Electron Device Letters, 2017, 38, 859-862.	3.9	48
21	Nanostructured GaN transistors. , 2017, , .		2
22	A low subthreshold swing tunneling field effect transistor for next generation low power CMOS applications. Physica E: Low-Dimensional Systems and Nanostructures, 2015, 74, 251-257.	2.7	10
23	Structural, dielectric and magnetic properties of Ta-substituted Bi _{0.8} La _{0.2} FeO ₃ multiferroics. Journal of Alloys and Compounds, 2015, 622, 471-476.	5.5	16
24	Physical/process parameter dependence of gate capacitance and ballistic performance of InAs _y Sb _{1-y} Quantum Well Field Effect Transistors. , 2013, , .		0
25	In _x Ga _{1-x} Sb MOSFET: Performance analysis by self consistent CV characterization and direct tunneling gate leakage current. , 2012, , .		2
26	Self-consistent C-V characterization of depletion mode buried channel InGaAs/InAs Quantum Well FET incorporating strain effects. , 2012, , .		0
27	A physically based analytical modeling of threshold voltage control for fully-depleted SOI double gate NMOS-PMOS Flexible-FET. , 2012, , .		0
28	Self consistent simulation of C-V characterization and ballistic performance of double gate SOI flexible-FET incorporating QM effects. , 2012, , .		0